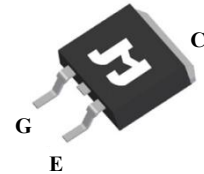


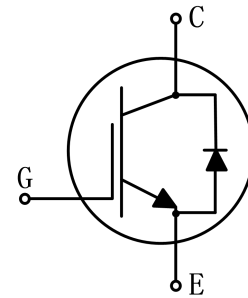
Key performance:

- $V_{CE}=650V$
- $I_C=6A@T_C=100^{\circ}C$
- $V_{CE(sat)}=1.7 V$

TO-263


Features:

- High ruggedness performance
- Very tight parameter distribution
- Positive $V_{CE(sat)}$ temperature coefficient
- High efficiency for motor control
- Excellent current sharing in parallel operation
- RoHS compliant


Applications:

- Home appliances
- Motor drives
- Fan, Pumps, Vacuum cleaner

Package parameters

Type	Marking	Package	Packaging method
JJT6N65SC	T0665SC	TO-263	Tape and reel



XXXX XXXX
 Wafer Lot Number Datecode-YYWW

Maximum ratings

Symbol	Parameter	Values	Unit
V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±20	V
I_C	Continuous collector current ($T_C=25^\circ\text{C}$)	12	A
	Continuous collector current ($T_C=100^\circ\text{C}$)	6	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	24	A
I_F	Diode continuous forward current ($T_C=100^\circ\text{C}$)	6	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	24	A
t_{sc}	Short circuit withstand time	10	µs
P_{tot}	Power dissipation ($T_C=25^\circ\text{C}$)	115	W
	Power dissipation ($T_C=100^\circ\text{C}$)	57	W
T_{vj}	Operating junction temperature range	-40 to +175	°C
T_{stg}	Storage temperature range	-55 to +150	°C

Thermal characteristics

Symbol	Parameter	Values		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	1.3	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	4.0	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	40	K/ W

Electrical characteristics of IGBT ($T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Static characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-emitter breakdown voltage	$V_{GE}=0\text{V}, I_C=250\mu\text{A}$	650	-	-	V
I_{CES}	Collector-emitter leakage current	$V_{CE}=650\text{V}, V_{GE}=0\text{V}$	-	-	10	μA
I_{GES}	Gate leakage current, forward	$V_{GE}=20\text{V}, V_{CE}=0\text{V}$	-	-	100	nA
	Gate leakage current, reverse	$V_{GE}=-20\text{V}, V_{CE}=0\text{V}$	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{GE}=V_{CE}, I_C=1\text{mA}$	5.7	6.2	6.7	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE}=15\text{V}, I_C=6\text{A}$	-	1.7	-	V
		$V_{GE}=15\text{V}, I_C=6\text{A}, T_{vj}=175^{\circ}\text{C}$	-	2.2	-	V

Dynamic characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
C_{ies}	Input capacitance	$V_{CE}=30\text{V}$ $V_{GE}=0\text{V}$ $f=1\text{MHz}$	-	480	-	pF
C_{oes}	Output capacitance		-	22	-	pF
C_{res}	Reverse transfer capacitance		-	8	-	pF
Q_g	Total gate charge	$V_{CC}=520\text{V}$ $V_{GE}=15\text{V}$ $I_C=6\text{A}$	-	19	-	nC

Switching characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=400V$ $V_{GE}=0/15V$ $I_C=6A$ $R_G=10\Omega$ Inductive load	-	10	-	ns
t_r	Rise time		-	8	-	ns
$t_{d(off)}$	Turn-off delay time		-	79	-	ns
t_f	Fall time		-	56	-	ns
E_{on}	Turn-on energy		-	0.11	-	mJ
E_{off}	Turn-off energy		-	0.10	-	mJ
E_{ts}	Total switching energy		-	0.21	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CC}=400V$ $V_{GE}=0/15V$ $I_C=6A$ $R_G=10\Omega$ Inductive Load $T_{vj}=175^\circ C$	-	11	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	108	-	ns
t_f	Fall time		-	89	-	ns
E_{on}	Turn-on energy		-	0.16	-	mJ
E_{off}	Turn-off energy		-	0.16	-	mJ
E_{ts}	Total switching energy		-	0.32	-	mJ

Electrical characteristics of Diode ($T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
V_F	Diode forward voltage	$I_F=6\text{A}$	-	1.6	-	V
		$I_F=6\text{A}, T_{vj}=175^{\circ}\text{C}$	-	1.4	-	V
t_{rr}	Diode reverse recovery time	$V_R=400\text{V}$ $I_F=6\text{A}$ $di_F/dt=-500\text{A}/\mu\text{s}$	-	55	-	ns
I_{rrm}	Diode peak reverse recovery current		-	10	-	A
Q_{rr}	Diode reverse recovery charge		-	306	-	nC
t_{rr}	Diode reverse recovery time	$V_R=400\text{V}$ $I_F=6\text{A}$ $di_F/dt=-500\text{A}/\mu\text{s}$ $T_{vj}=175^{\circ}\text{C}$	-	98	-	ns
I_{rrm}	Diode peak reverse recovery current		-	12	-	A
Q_{rr}	Diode reverse recovery charge		-	529	-	nC

Typical performance characteristics

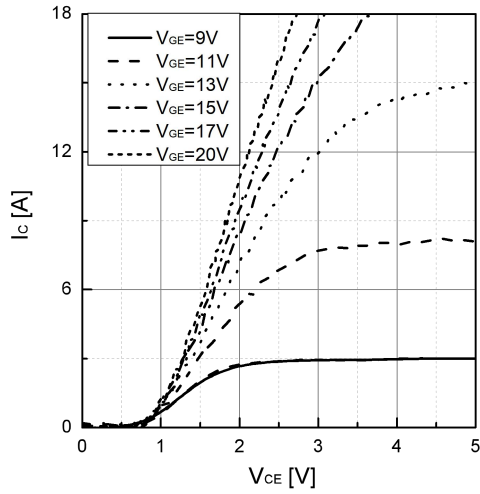


Fig 1. Typical output characteristic ($T_{vj}=25^{\circ}\text{C}$)

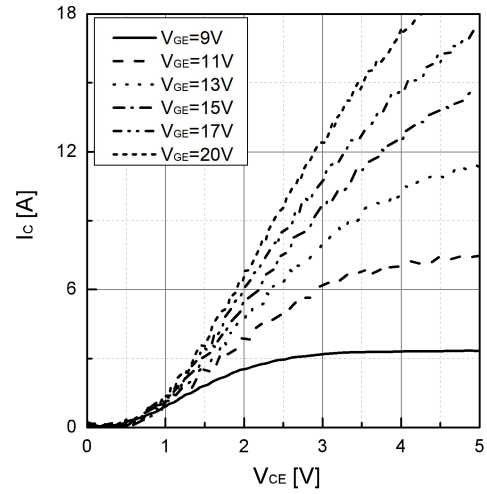


Fig 2. Typical output characteristic ($T_{vj}=175^{\circ}\text{C}$)

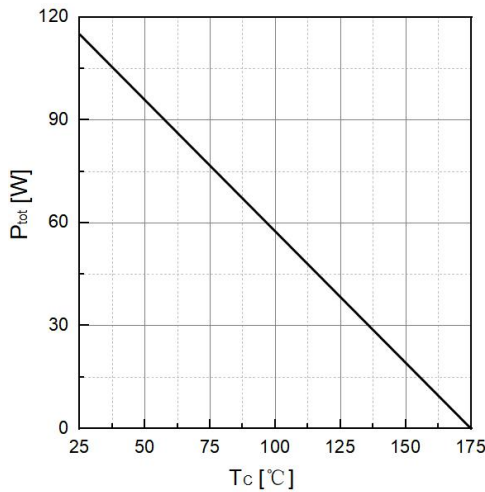


Fig 3. Power dissipation as a function of T_c

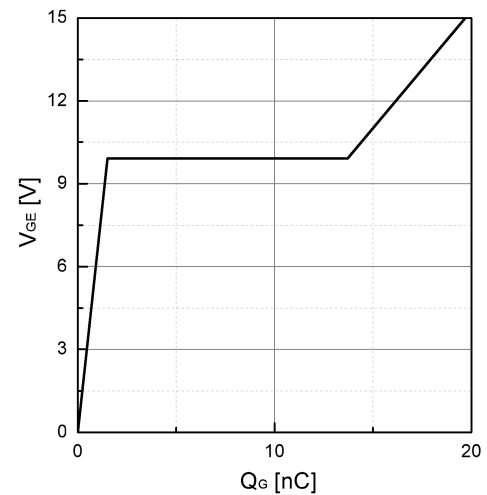


Fig 4. Typical Gate charge

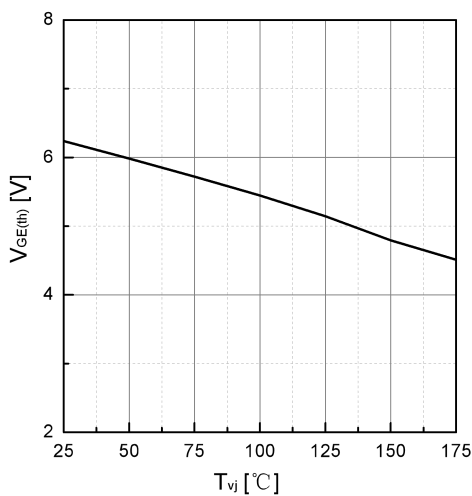


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj}
($I_C=1\text{mA}$)

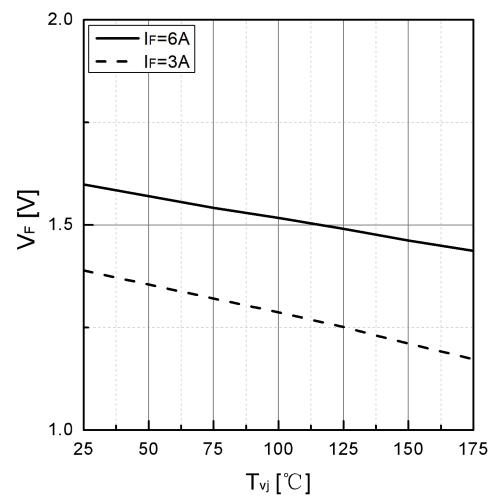


Fig 6. Typical V_F as a function of T_{vj}

Typical performance characteristics

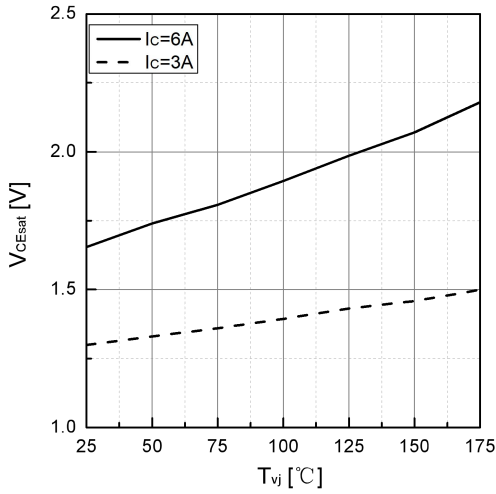


Fig 7. Typical V_{CEsat} as a function of T_{vj}

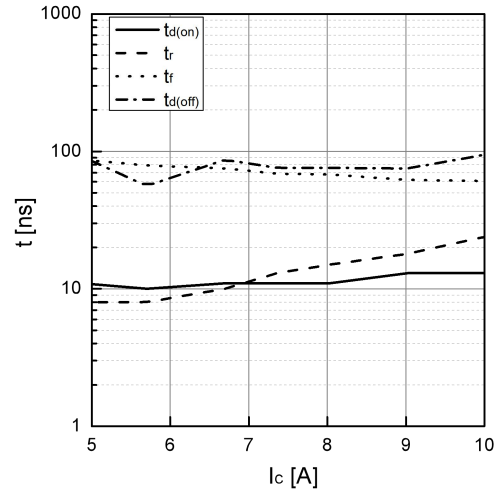


Fig 8. Typical switching time as a function of I_c

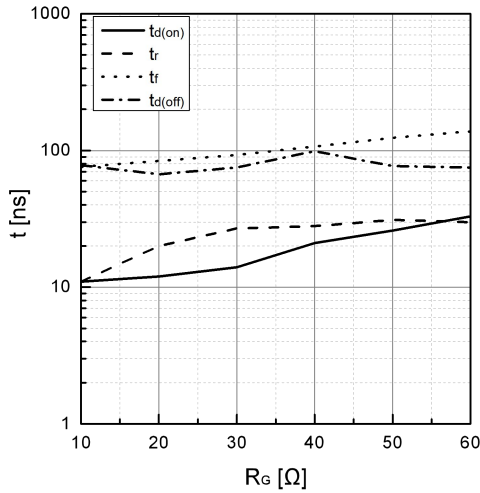


Fig 9. Typical switching times as a function of R_G

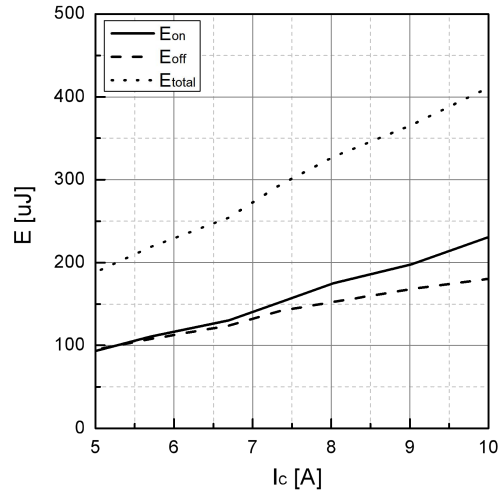


Fig 10. Typical switching energy losses as a function of I_c

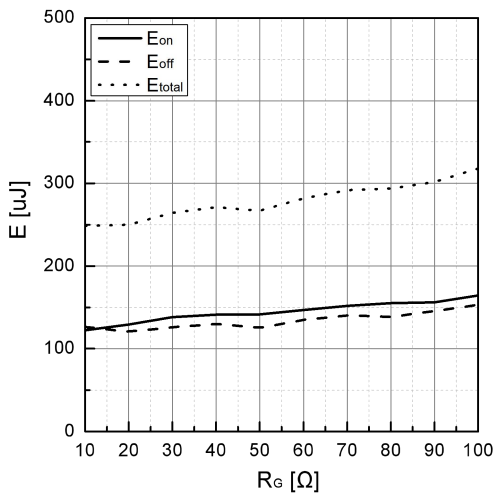


Fig 11. Typical switching energy losses as a function of R_G

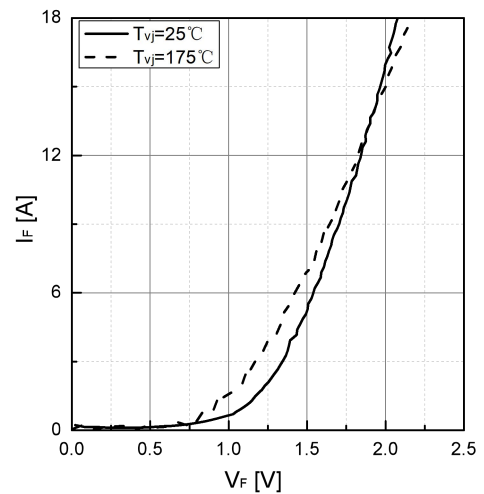


Fig 12. Typical I_F as a function of V_F

Typical performance characteristics

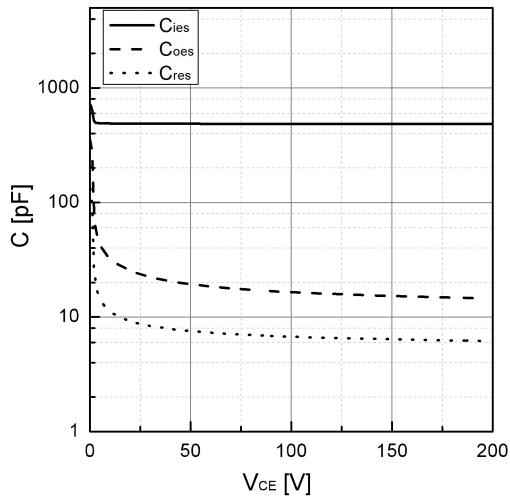


Fig 13. Typical capacitance as a function of V_{CE}
($f=1\text{MHz}$, $V_{GE}=0\text{V}$)

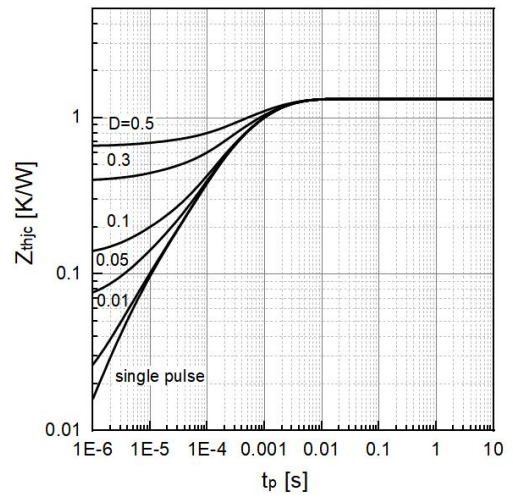
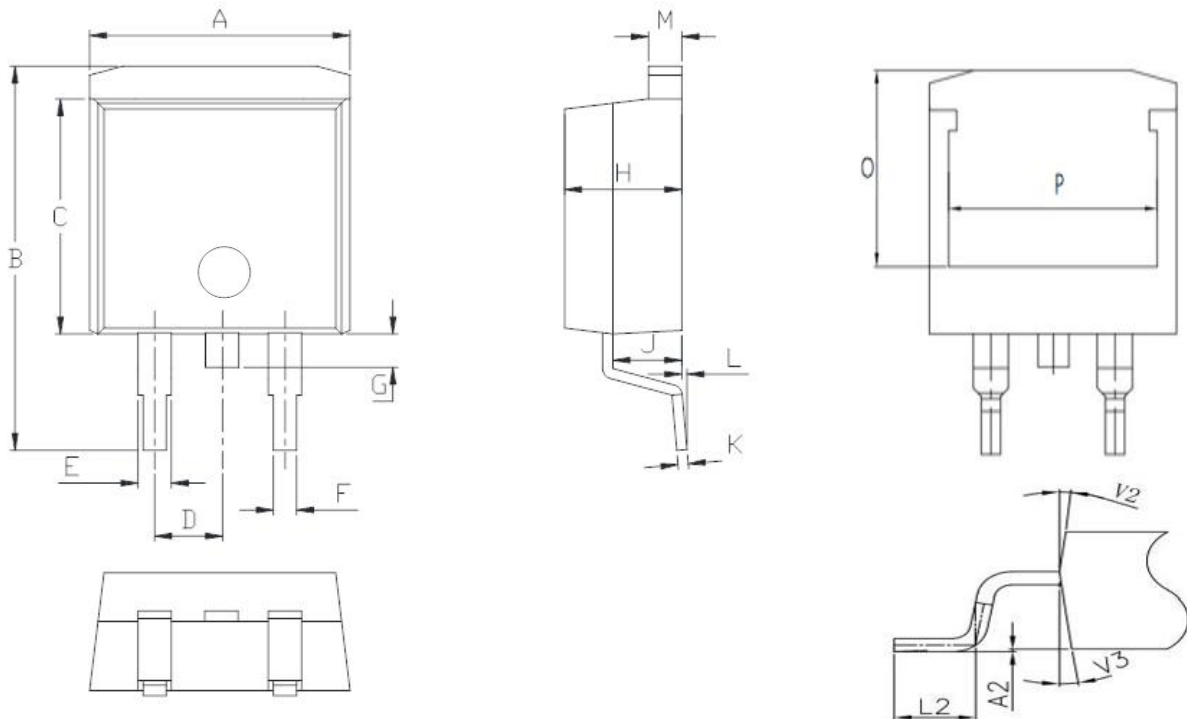


Fig 14. Transient thermal impedance of IGBT

Package dimension

TO-263



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90	-	10.20	0.390	-	0.402
B	14.70	-	15.80	0.579	-	0.622
C	8.8	-	9.4	0.346	-	0.370
D	-	2.54	-	-	0.100	-
E	1.37	-	1.57	0.054	-	0.062
F	0.75	-	0.85	0.029	-	0.033
G	-	-	1.75	-	-	0.069
H	4.30	-	4.70	0.169	-	0.185
J	2.30	-	2.70	0.091	-	0.106
K	0.38	-	0.55	0.015	-	0.022
L	0	0.15	0.25	0	0.006	0.010
M	1.25	-	1.35	0.049	-	0.053
O	7.4	7.65	7.9	0.291	0.301	0.311
P	8.3	8.6	8.9	0.327	0.339	0.350
L2	2.20	2.35	2.50	0.087	0.093	0.098

Revision history

Date	Revision	Changes
2024-06-25	Rev 1.0	Release of the datasheet
2025-02-06	Rev 1.1	Update
2025-04-08	Rev 1.2	Character Update
2025-12-23	Rev 1.3	Add marking specification
2026-03-12	Rev 1.4	Update POD
2026-06-23	Rev 1.5	Update thermal

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